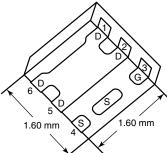
Vishay Siliconix

N-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)					
12	0.019 at V _{GS} = 4.5 V	9						
	0.022 at V _{GS} = 2.5 V	9	9.6 nC					
	0.026 at V _{GS} = 1.8 V		9.0110					
	0.065 at V _{GS} = 1.2 V	3						

PowerPAK SC-75-6L-Single





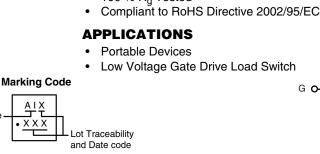
<u>AIX</u> Part # code XXX

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.75 mm Profile
 - 100 % R_a Tested



RoHS COMPLIANT HALOGEN FREE



N-Channel MOSFET

D

Ordering Information: SiB404DK-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	12	N/
Gate-Source Voltage		V _{GS}	± 5	- V
	T _C = 25 °C		9 ^a	
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 70 °C		9 ^a	
Continuous Drain Current $(1_j = 150 \text{ C})$	T _A = 25 °C	I _D	8.9 ^{b, c}	
	T _A = 70 °C		7.1 ^{b, c}	А
Pulsed Drain Current	·	I _{DM}	35	
Continuous Courses Drain Diada Current	T _C = 25 °C	1	9 ^a	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.1 ^{b, c}	
	T _C = 25 °C		13	
Maximum Davier Dissingtion	T _C = 70 °C		8.4	w
Maximum Power Dissipation	T _A = 25 °C	P _D	2.5 ^{b, c}	vv
	T _A = 70 °C	1 [1.6 ^{b, c}	7
Operating Junction and Storage Temperature Ra	nge	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE BATINGS

Parameter	Symbol	Symbol Typical		Unit						
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	41	51	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5	C/ W					

Notes:

a. Package limited, $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.

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Parameter	Symbol Test Conditions			Тур.	Max.	Unit	
Static	•				•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	12			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		12		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	i _D = 250 μA		- 2.5		mv/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.35		0.8	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 5 V$			± 100	nA	
Zara Cata Valtaga Drain Current	1	V _{DS} = 12 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 12 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	15			A	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3 \text{ A}$		0.015	0.019	Ω	
	P	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 2 \text{ A}$		0.018	0.022		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 1.8 V, I _D = 1 A		0.021	0.026		
		V _{GS} = 1.2 V, I _D = 0.5 A		0.035	0.065		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 3 A		30		S	
Dynamic ^b	•		•			•	
Total Gate Charge	Qg			9.6	15		
Gate-Source Charge	Q _{gs}	$V_{DS} = 6 V, V_{GS} = 4.5 V, I_{D} = 9 A$		0.9		nC	
Gate-Drain Charge	Q _{gd}			1.7			
Gate Resistance	R _g	f = 1 MHz	0.6	3.2	6.4	Ω	
Turn-On Delay Time	t _{d(on)}			5	10		
Rise Time	t _r	V_{DD} = 6 V, R_L = 0.86 Ω		20	40		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 7 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		20	40	ns	
Fall Time	t _f			10	20		
Drain-Source Body Diode Characteristic	s		•			•	
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			9	٨	
Pulse Diode Forward Current	Diode Forward Current I _{SM}				35	A	
Body Diode Voltage	V _{SD}	I _S = 7 A, V _{GS} = 0 V		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L = 7.4 dt/dt = 100.4/up T = 25.00		5	10	nC	
Reverse Recovery Fall Time	t _a	l _F = 7 A, dl/dt = 100 A/μs, T _J = 25 °C		8			
Reverse Recovery Rise Time	t _b	1		7		ns	

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

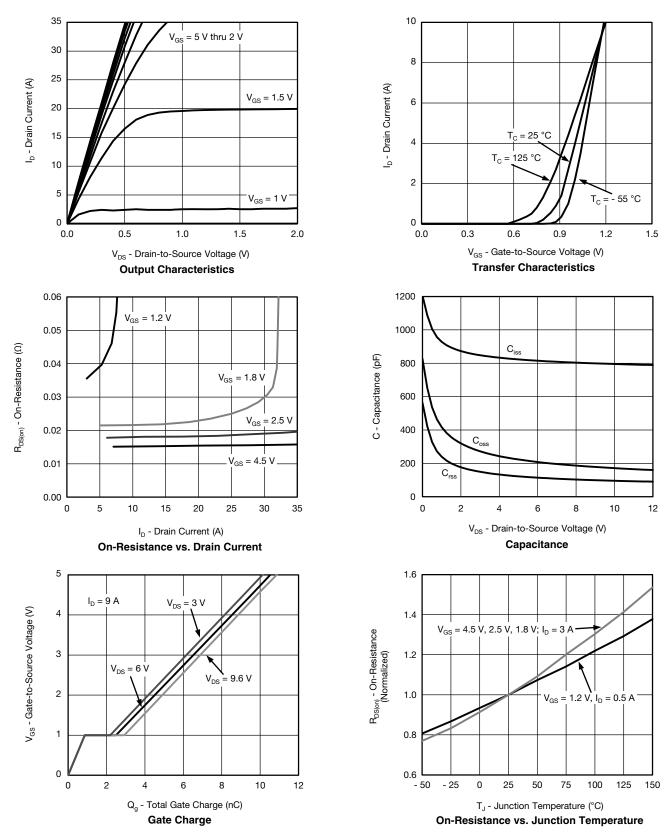
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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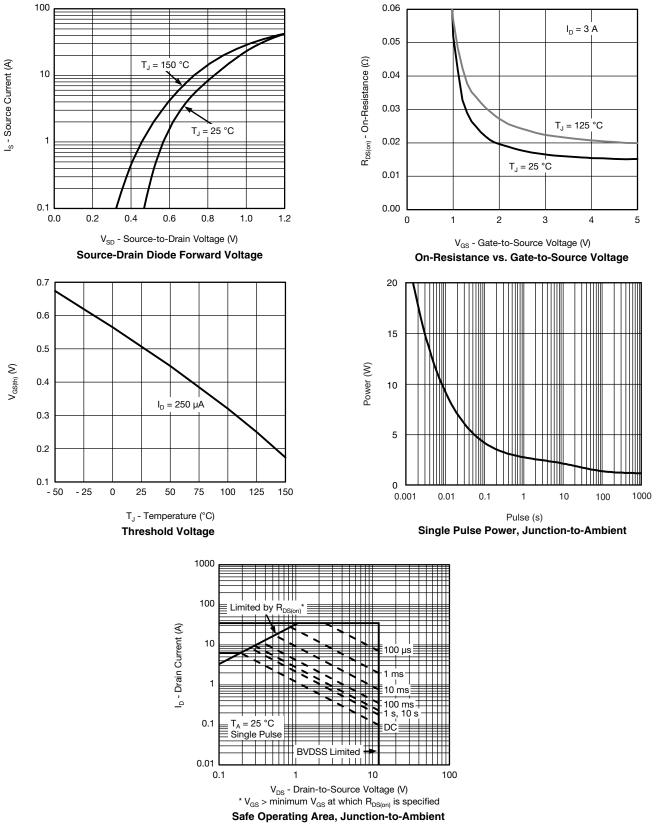
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



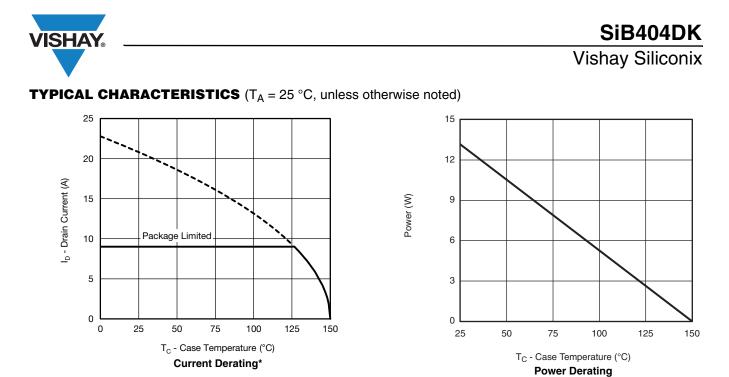
Document Number: 67099 S11-0236-Rev. A, 14-Feb-11

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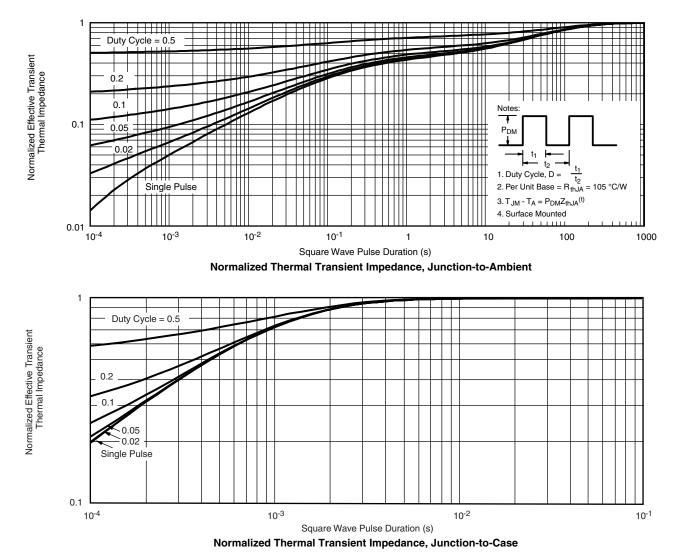


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

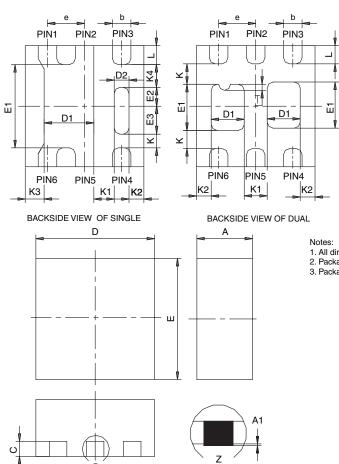


Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67099.

Package Information

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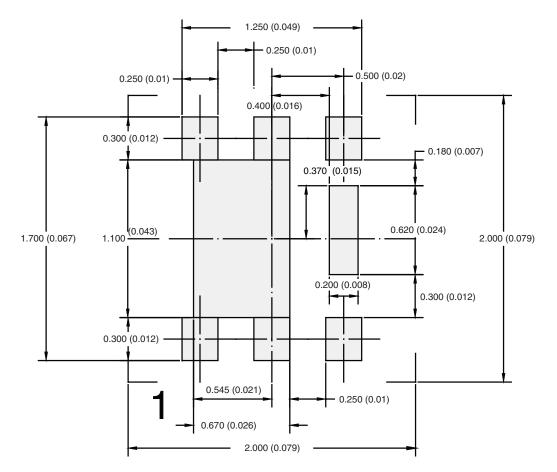
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC			0.020 BSC		0.50 BSC			0.020 BSC		
К		0.180 TYP			0.007 TYP		0.245 TYP			0.010 TYP		
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP		
K2	0.200 TYP				0.008 TYP		0.200 BSC		0.008 TYP			
K3	0.255 TYP		0.010 TYP									
K4	0.300 TYP		0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935												



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC75-6L Single



Dimensions in mm/(Inches)

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Revision: 01-Jan-2025

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